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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/623,918	07/21/2003	Tai-Su Park	8836-138 DIV (IE10162-US)	5372
75	90 08/05/	2004	EXAM	INER
Frank Chau, E	Sq.	OWENS, DO	OWENS, DOUGLAS W	
F. CHAU & AS	SOCIATES, LL			
Suite 501	•		ART UNIT	PAPER NUMBER
1900 Hempstea	d Turnpike	2811		
East Meadow,	NY 11554		DATE MAILED: 08/05/200	4

Please find below and/or attached an Office communication concerning this application or proceeding.

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	Application No.	Applicant(s)	
	10/623,918	PARK, TAI-SU	
Office Action Summary	Examiner	Art Unit	
	Douglas W Owens	2811	
The MAILING DATE of this communicated Period for Reply	ntion appears on the cover sheet wi	th the correspondence addres	is
A SHORTENED STATUTORY PERIOD FOR THE MAILING DATE OF THIS COMMUNICATION - Extensions of time may be available under the provisions of after SIX (6) MONTHS from the mailing date of this communication of the period for reply specified above is less than thirty (30) of the period for reply is specified above, the maximum statutes are to reply within the set or extended period for reply will any reply received by the Office later than three months after earned patent term adjustment. See 37 CFR 1.704(b).	ATION.  37 CFR 1.136(a). In no event, however, may a recation.  Idays, a reply within the statutory minimum of thirty ory period will apply and will expire SIX (6) MON'  1, by statute, cause the application to become AB.	eply be timely filed  (30) days will be considered timely.  THS from the mailing date of this commu  ANDONED (35 U.S.C. § 133).	nication.
Status			
1) Responsive to communication(s) filed	on .		
·	)⊠ This action is non-final.		
3) Since this application is in condition for	r allowance except for formal matte	ers, prosecution as to the me	rits is
closed in accordance with the practice	under Ex parte Quayle, 1935 C.D	11, 453 O.G. 213.	
Disposition of Claims			
4) Claim(s) 6-17 is/are pending in the app	olication.		
4a) Of the above claim(s) is/are	withdrawn from consideration.		
5)⊠ Claim(s) <u>9-17</u> is/are allowed.			
6)⊠ Claim(s) <u>6-8</u> is/are rejected.			
7) Claim(s) is/are objected to.			
8) Claim(s) are subject to restriction	on and/or election requirement.		
Application Papers			
9) ☐ The specification is objected to by the B	Examiner.		
10)⊠ The drawing(s) filed on 21 July 2003 is	/are: a)⊠ accepted or b)⊡ objec	ted to by the Examiner.	
Applicant may not request that any objection	on to the drawing(s) be held in abeyan	ce. See 37 CFR 1.85(a).	
Replacement drawing sheet(s) including th	e correction is required if the drawing(	s) is objected to. See 37 CFR 1	.121(d).
11)☐ The oath or declaration is objected to b	y the Examiner. Note the attached	Office Action or form PTO-1	52.
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for a) All b) Some * c) None of:		119(a)-(d) or (f).	
1. Certified copies of the priority do			
2. Certified copies of the priority do		·	
	the priority documents have been	received in this National Stag	ge
application from the Internationa			
* See the attached detailed Office action to	for a list of the certified copies not	received.	
Attachment(s)  1) Notice of References Cited (PTO-892)	4) 🗀 Intonview S	ummary (PTO-413)	
<ul> <li>1) Notice of References Cited (PTO-892)</li> <li>2) Notice of Draftsperson's Patent Drawing Review (PTO-892)</li> </ul>	)-948) Paper No(s	)/Mail Date	
3) Information Disclosure Statement(s) (PTO-1449 or PT	TO/SB/08) 5) Notice of Ir	formal Patent Application (PTO-152	2)
Paper No(s)/Mail Date	6)	<u> </u>	

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#### **DETAILED ACTION**

# Suggested Claim Amendments

1. It is suggested that the word "planarizing" in line 3 of claim 7 be deleted and replaced with --a second planarization step--.

## Claim Rejections - 35 USC § 102

2. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.
- 3. Claims 6 8 are rejected under 35 U.S.C. 102(e) as being anticipated by US Patent Application Publication No. 2002/0005560 to Lee et al.

Regarding claim 6, Lee et al. teach a method for forming a trench isolation (Figs. 10 - 16) comprising the steps of:

forming a planarization stop layer (140) on a semiconductor substrate (100) on which a pad oxide (120) is formed;

forming a trench (220) in the semiconductor substrate by etching sequentially a part of the planarization stop layer, a part of the pad oxide film, and a part of the semiconductor substrate (paragraph [0025]);

performing a thermal oxidation process (paragraph [0026]);

filling the trench with a trench fill insulating material ((400); paragraph [0027]);

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planarizing the trench fill material such that the planarization stop layer is exposed (Fig. 14; paragraph [0028]);

recessing the trench fill insulating material to under the planarization stop film, where the term "under the planarization stop film" is understood to mean an upper surface of the trench fill is lower than an upper surface of the planarization stop film; and

forming a trench oxidation-preventive film (500; paragraph [0029] (silicon nitride performs the function of oxidation prevention)).

Regarding claim 7, Lee et al. teach a method, wherein the level of the trench oxidation-preventive film is substantially even with an upper surface of the planarization stop film after planarizing (Fig. 16).

Regarding claim 8, Lee et al. teach a method, wherein the planarization stop film is made of a silicon layer (paragraph [0024]), and the trench oxidation-preventive film is made of a silicon nitride film (paragraph [0029]).

## Allowable Subject Matter

- 4. Claims 9 17 are allowed.
- 5. The following is a statement of reasons for the indication of allowable subject matter: The prior art of record does not teach, alone or in combination, a method of forming a trench isolation including forming a thermal oxide on a sidewall and top surface of the planarization stop film.

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#### Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Douglas W Owens whose telephone number is 571-272-1662. The examiner can normally be reached on Monday-Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Eddie C Lee can be reached on 571-272-1732. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Douglas W. Owens

Dough L. Owa-

**Patent Examiner**